

N-Channel JFET, Dual

-25 V, 20 to 40 mA, 40 mS

NSVJ6904DSB6

The NSVJ6904DSB6 is a composite type of JFET designed for compact size and high efficiency which can achieve high gain performance. This AEC-Q101 qualified and PPAP capable device is suited for automotive applications.

Features

- Large $|y_{fs}|$
- Small Ciss
- Ultralow Noise Figure
- CPH6 Package is Pin-Compatible with SC-74
- AEC-Q101 Qualified and PPAP Capable
- Mounting Area is Greatly Reduced by Incorporating Two JFETs of the NSVJ3910SB3 in One Package of CPH6 Compared with Using Two Separate Packages

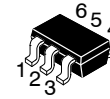
Typical Applications

- AM Tuner RF Amplification
- Low Noise Amplifier

SPECIFICATIONS ABSOLUTE MAXIMUM RATINGS $T_A = 25^\circ\text{C}$

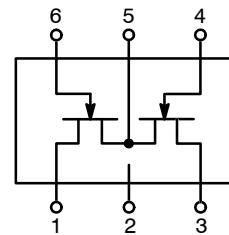
Symbol	Parameter	Value	Unit
V_{DSX}	Drain to Source Voltage	25	V
V_{GDS}	Gate to Drain Voltage	-25	V
I_G	Gate Current	10	mA
I_D	Drain Current	50	mA
P_D	Allowable Power Dissipation 1 unit	400	mW
P_T	Total Power Dissipation	700	mW
T_J, T_{Stg}	Operating Junction and Storage Temperature	-55 to +150	$^\circ\text{C}$

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.



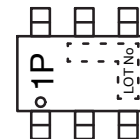
CPH6
CASE 318BD

ELECTRICAL CONNECTION N-Channel



- 1 : Drain 1
- 2 : NC
- 3 : Drain 2
- 4 : Gate 2
- 5 : Source 1 / Source 2
- 6 : Gate 1

MARKING DIAGRAM



CPH6

ORDERING INFORMATION

See detailed ordering, marking and shipping information in the package dimensions section on page 4 of this data sheet.

NSVJ6904DSB6

ELECTRICAL CHARACTERISTICS $T_J = 25^\circ\text{C}$ (Note 1)

Symbol	Characteristic	Conditions	Min	Typ	Max	Unit
$V_{(BR)GDS}$	Gate to Drain Breakdown Voltage	$I_G = -10\ \mu\text{A}$, $V_{DS} = 0\ \text{V}$	-25	-	-	V
I_{GSS}	Gate to Source Leakage Current	$V_{GS} = -10\ \text{V}$, $V_{DS} = 0\ \text{V}$	-	-	-1.0	nA
$V_{GS(off)}$	Cutoff Voltage	$V_{DS} = 5\ \text{V}$, $I_D = 100\ \mu\text{A}$	-0.6	-1.2	-1.8	V
I_{DSS}	Zero-Gate Voltage Drain Current	$V_{DS} = 5\ \text{V}$, $V_{GS} = 0\ \text{V}$	20	-	40	mA
$ y_{fs} $	Forward Transfer Admittance	$V_{DS} = 5\ \text{V}$, $V_{GS} = 0\ \text{V}$, $f = 1\ \text{kHz}$	30	40	-	mS
C_{iss}	Input Capacitance	$V_{DS} = 5\ \text{V}$, $V_{GS} = 0\ \text{V}$, $f = 1\ \text{MHz}$	-	6.0	-	pF
C_{rss}	Reverse Transfer Capacitance		-	2.3	-	pF
NF	Noise Figure	$V_{DS} = 5\ \text{V}$, $V_{GS} = 0\ \text{V}$, $f = 100\ \text{MHz}$	-	2.1	2.8	dB

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

1. The specifications shown above are for each individual JFET.

TYPICAL CHARACTERISTICS

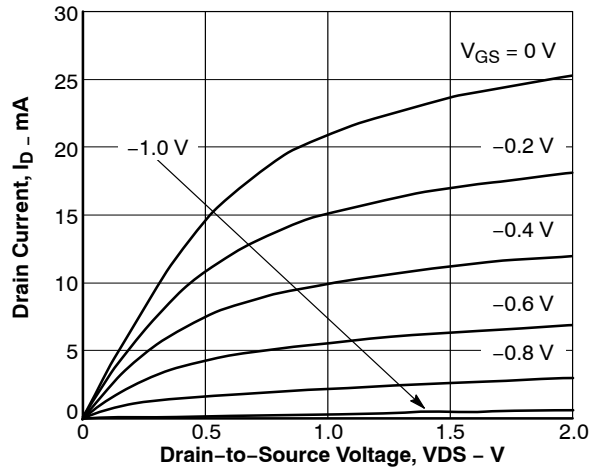


Figure 1. $I_D - V_{DS}$

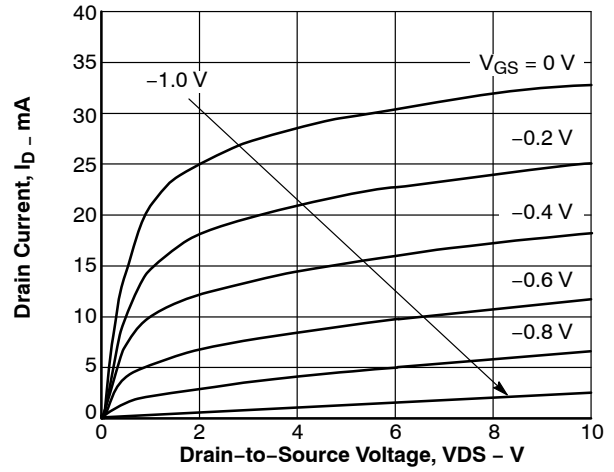


Figure 2. $I_D - V_{DS}$

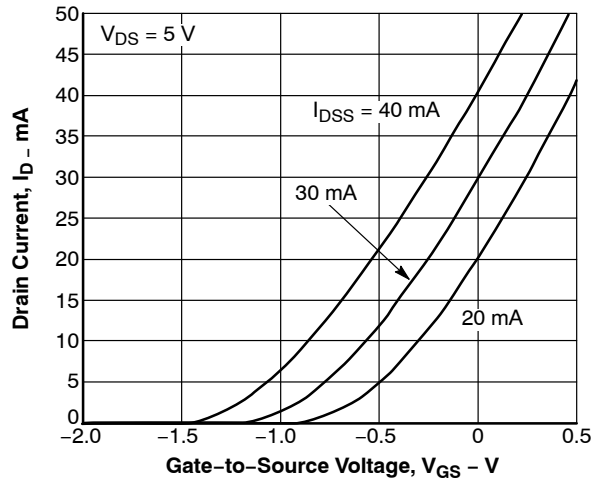


Figure 3. $I_D - V_{GS}$

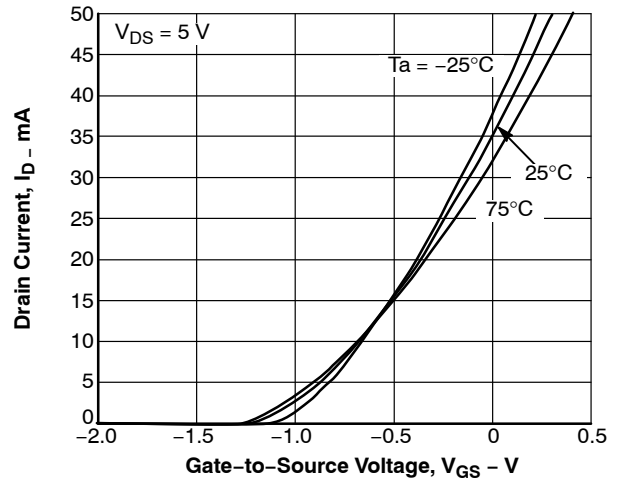


Figure 4. $I_D - V_{GS}$

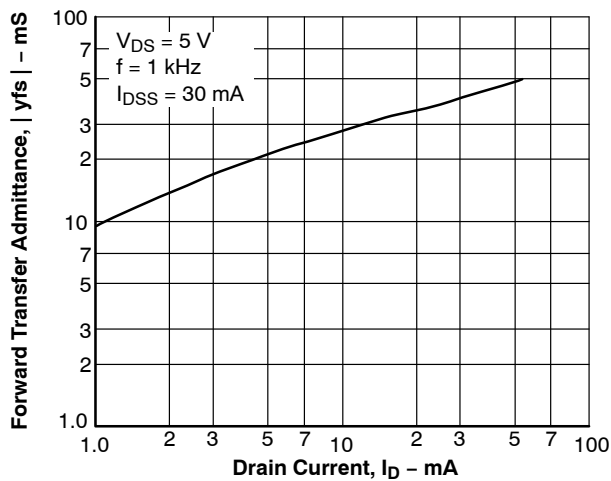


Figure 5. $|y_{fs}| - I_D$

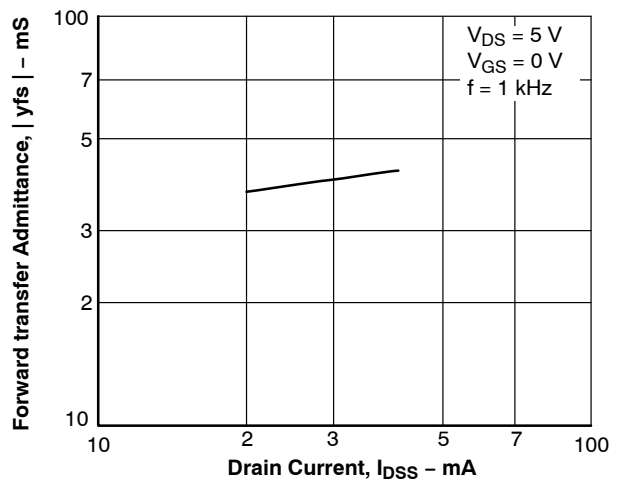


Figure 6. $|y_{fs}| - I_{DSS}$

TYPICAL CHARACTERISTICS (continued)

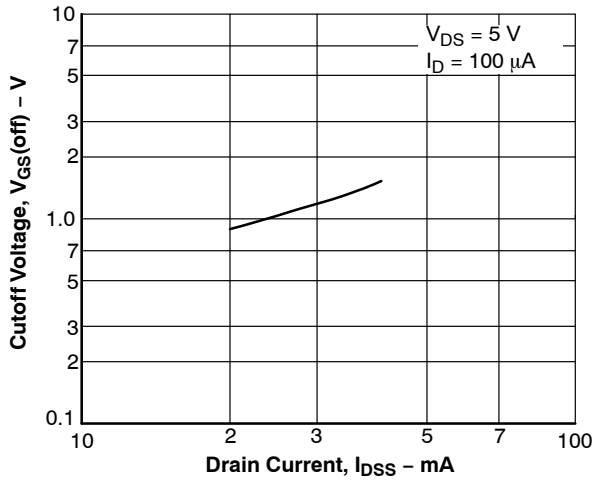


Figure 7. $V_{GS(off)} - I_{DSS}$

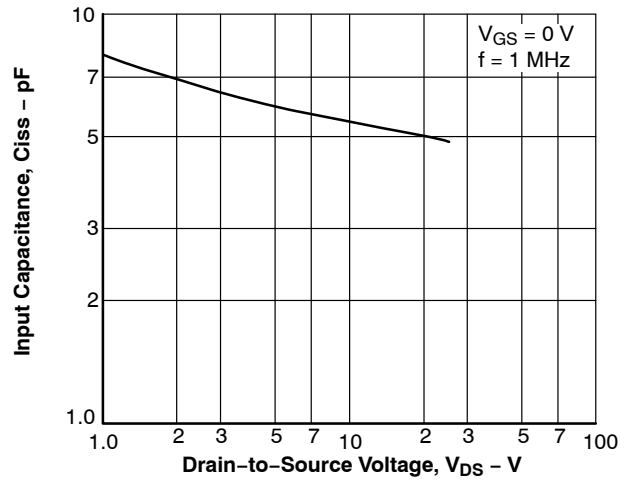


Figure 8. $C_{iss} - V_{GDS}$

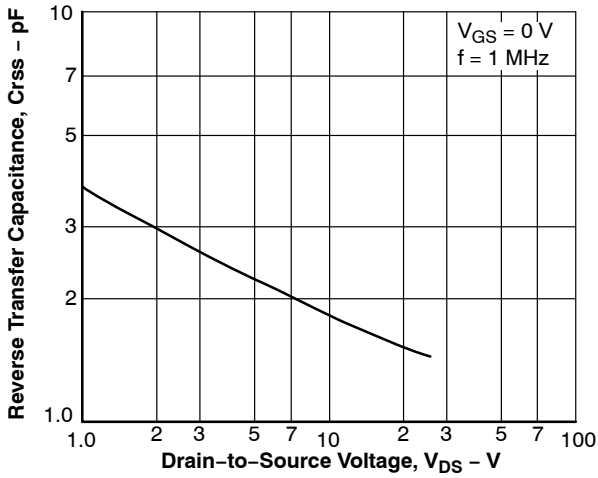


Figure 9. $C_{rss} - V_{DS}$

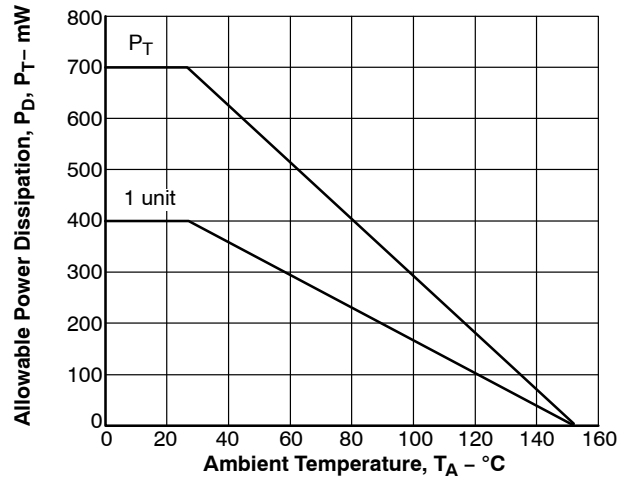


Figure 10. $P_D, P_T - T_A$

ORDERING INFORMATION

Device Order Number	Specific Device Marking	Package Type	Shipping [†]
NSVJ6904DSB6T1G	1P	CPH6 (Pb-Free / Halogen Free)	3,000 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, [BRD8011/D](#).

MECHANICAL CASE OUTLINE

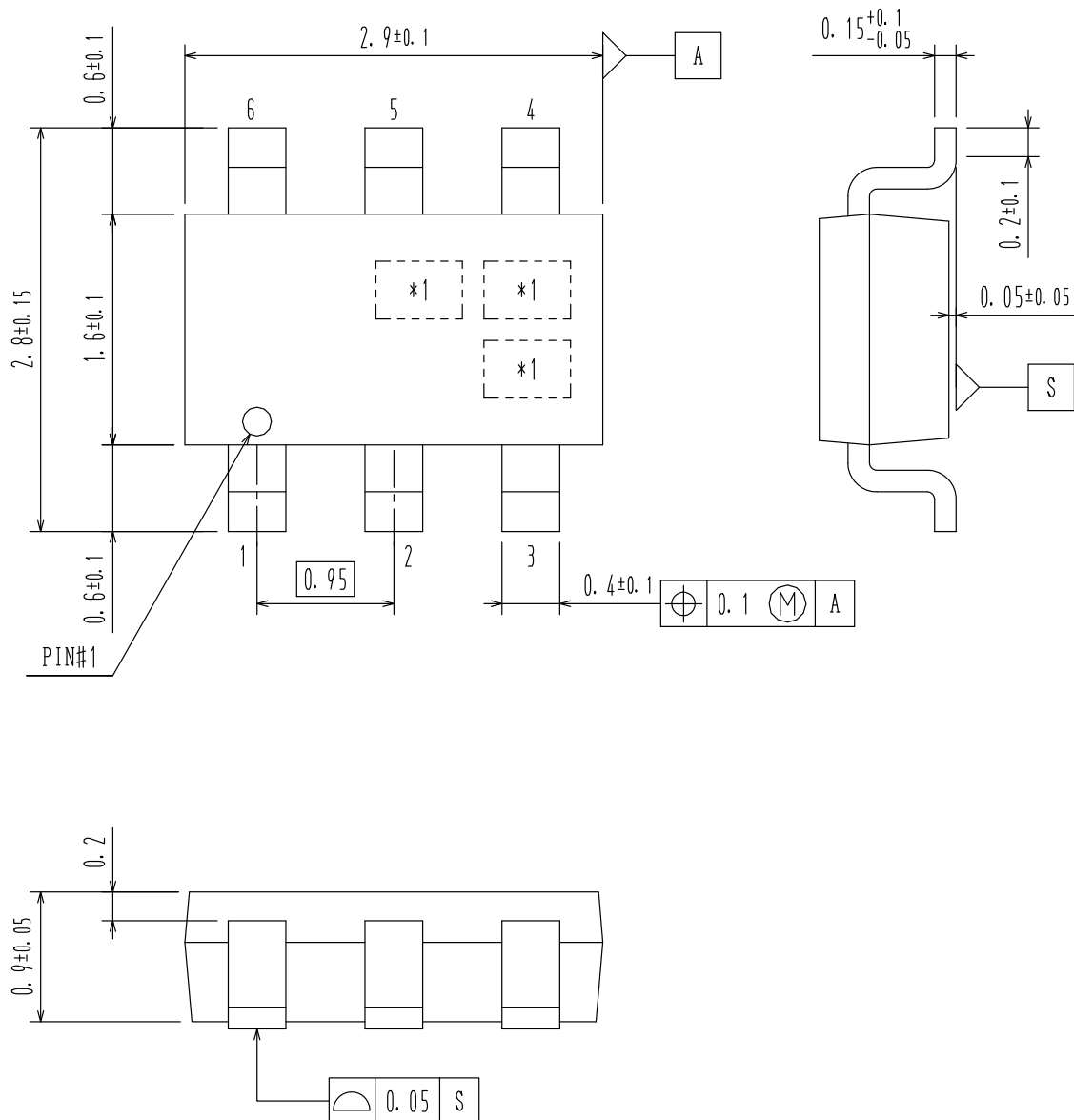
PACKAGE DIMENSIONS

ON Semiconductor®


ON

CPH6
CASE 318BD
ISSUE O

DATE 30 NOV 2011



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